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APPROVAL SHEET

Part No: **BF3H01G-NPT**

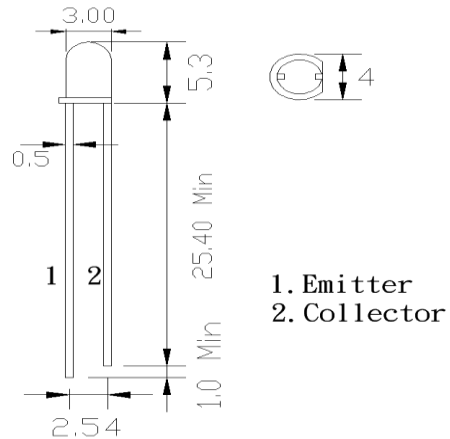
NOTE : Green Part

MAKER			CUSTOMER	
				
R&D	QA	Sales	Checked	Approved
				

Prepared	Checked	Approved
Rachel Lee	Sky Lin	Kenneth Wu

DESCRIPTION:

Device Type : BF3H01G-NPT
 Dice Material : Silicon
 Lens Color : Black
 Lens Dimension : 3 mm



All epoxy resin dimension are in millimeter
 tolerance is $\pm 0.2\text{mm}$

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Rating.	Unit
Power dissipation	Pd	75	mW
Operating Temperature	Topr	-40 ~ +80	°C
Storage Temperature	Tstr	-40 ~ +100	°C
Solder DIP (MAX. 5 seconds, 1.6mm from body) Temperature 260°C			

Electrical and Optical Characteristics at Ta=25°C

Description	Symbol	Condition	Min.	Typ.	Max.	Unit
Range of Spectral Bandwid	Wp		400	-	1100	nm
Peak sensitive wavelength	Wp		-	940	-	nm
C-E breakdown voltage	BV _{CEO}	I _C =100uA	30	-	-	V
E-C breakdown voltage	BV _{ECO}	I _E =100uA	5	-	-	V
Collector dark current	I _{CEO}	V _{CE} =20V	-	-	100	nA
C-E saturation voltage	V _{CE(sat)}	I _C = 2mA / I _B =100uA	-	-	0.2	V
Light Current	I _L	E _e =1mW/C m ² V _{CE} =5V	0.7	-	-	mA
Rise Time	t _r	V _{CE} =5V I _C =1mA	-	15	-	μS
Fall Time	t _f	R _L =1000Ω	-	15	-	

- Note:**
- The lead should be formed up to 5mm from the body of device without forming stress.
 - Soldering shall be performed after lead forming.
 - All dimensions are in millimeters

LED LAMP Technical Data

Typical Optical-Electrical Characteristic Curves

